



HM6718

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The HM6718 is designed for general purpose medium power amplifier and switching.

Features

- High power: 1W
- High current: 1A

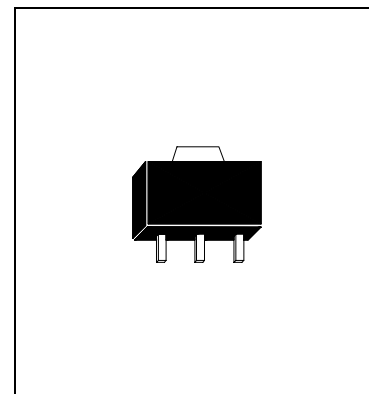
Absolute Maximum Ratings

- Maximum Temperatures
Storage Temperature -55 ~ +150 °C
Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
Total Power Dissipation (Ta=25°C) 1 W
- Maximum Voltages and Currents (Ta=25°C)
VCBO Collector to Base Voltage 100 V
VCEO Collector to Emitter Voltage 100 V
VEBO Emitter to Base Voltage 5 V
IC Collector Current 1 A

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	100	-	-	V	IC=100uA
BVCEO	100	-	-	V	IC=1mA
BVEBO	5	-	-	V	IE=10uA
ICBO	-	-	100	nA	VCB=80V
*VCE(sat)	-	-	350	mV	IC=350mA, IB=35mA
*hFE1	80	-	-		VCE=1V, IC=50mA
*hFE2	100	-	250		VCE=1V, IC=250mA
*hFE3	20	-	-		VCE=1V, IC=500mA
fT	50	-	-	MHz	VCE=10V, IC=50mA, f=100MHz
Cob	-	-	20	pF	VCB=10V, f=1MHz

*Pulse Test : Pulse Width ≤380us, Duty Cycle≤2%





Characteristics Curve

